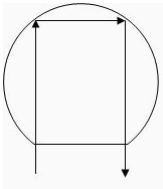


Part Number	Customer
-------------	----------

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm	
	2.0	Primary Flat Orientation	{110}+/-1 degree	Wafer Vendor
	3.0	Primary Flat Length	32.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	
	5.0	Overall Thickness	360.00 +/- 10.00 μm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<5.00μm	Guaranteed by Process
	7.0	Bow	<60.00μm	ADE to ASTM F534, 20%
	8.0	Warp	<60.00μm	ADE to ASTM F657, 20%
	9.0	Edge Chips	0	Bright Light, 100%
	10.0	Edge Exclusion	5mm	
HandleSilicon	11.0	Handle Growth Method	CZ	Wafer Vendor
	12.0	Handle Orientation	{111} +/- 0.5 degree	Wafer Vendor
	13.0	Handle Thickness	360.00 +/- 10.00 μm	ADE, 100%
	14.0	Handle Doping Type	N	Wafer Vendor
	15.0	Handle Dopant	Phos	Wafer Vendor
	16.0	Handle Resistivity	0.003-0.01 Ohm-cm	Wafer Vendor
	17.0	Frontside Finish	Polished (Prime)	Guaranteed by process
	18.0	Backside Finish	Polished with lasermark and light handline marks	Guaranteed by process
	19.0	Total scratch length	Frontside - None	Bright Light, 100% (note2)
	20.0	Surface Haze	none	Bright Light, 100% (note 2)

Part Number	Customer
-------------	----------

Category	Parameter	Specification	Measurement Method
----------	-----------	---------------	--------------------

Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

Explanatory Notes	1. Microscope inspection performed using microscope scan as below. 5x objective.		
	2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.		
	3. 9 point measurement are as shown in the diagram below:		



Additional Information